

74LV00

Quad 2-input NAND gate

Rev. 03 — 20 December 2007

Product data sheet

1. General description

The 74LV00 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC00 and 74HCT00.

The 74LV00 provides a quad 2-input NAND function.

2. Features

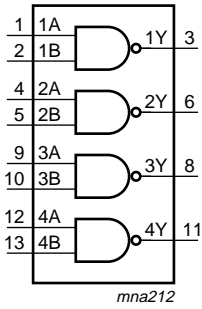
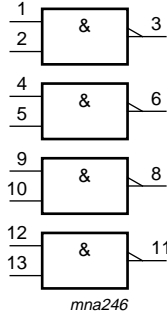
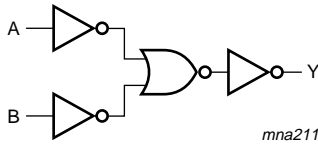
- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between $V_{CC} = 2.7$ V and $V_{CC} = 3.6$ V
- Typical output ground bounce < 0.8 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

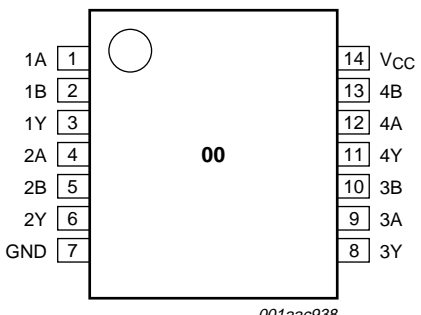
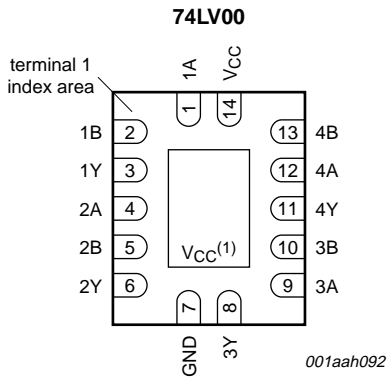
Type number	Package			
	Temperature range	Name	Description	Version
74LV00N	-40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74LV00D	-40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LV00DB	-40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74LV00PW	-40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LV00BQ	-40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

4. Functional diagram

 <p><i>mna212</i></p>	 <p><i>mna246</i></p>	 <p><i>mna211</i></p>
<p>Fig 1. Logic symbol</p>	<p>Fig 2. IEC logic symbol</p>	<p>Fig 3. Logic diagram (one gate)</p>

5. Pinning information

5.1 Pinning

 <p><i>001aac938</i></p>	<p>74LV00</p>  <p><i>001aah092</i></p> <p>Transparent top view</p> <p>(1) The die substrate is attached to this pad using conductive die attach material. It can not be used as a supply pin or input.</p>
<p>Fig 4. Pin configuration DIP14, SO14 and (T)SSOP14</p>	<p>Fig 5. Pin configuration DHVQFN14</p>

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output

Table 2. Pin description ...continued

Symbol	Pin	Description
GND	7	ground (0 V)
3Y	8	data output
3A	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table^[1]

Input		Output
nA	nB	nY
L	X	H
X	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V}$ or $V_I > V_{CC} + 0.5 \text{ V}$	[1] -	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{CC} + 0.5 \text{ V}$	[1] -	±50	mA
I _O	output current	$V_O = -0.5 \text{ V}$ to $(V_{CC} + 0.5 \text{ V})$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C			
		DIP14 package	[2] -	750	mW
		SO14 package	[3] -	500	mW
		(T)SSOP14 package	[4] -	500	mW
		DHVQFN14 package	[5] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 12 mW/K above 70 °C.

[3] P_{tot} derates linearly with 8 mW/K above 70 °C.

[4] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[5] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		[1] 1.0	3.3	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.0\text{ V to }2.0\text{ V}$	-	-	500	ns/V
		$V_{CC} = 2.0\text{ V to }2.7\text{ V}$	-	-	200	ns/V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	100	ns/V
		$V_{CC} = 3.6\text{ V to }5.5\text{ V}$	-	-	50	ns/V

[1] The static characteristics are guaranteed from $V_{CC} = 1.2\text{ V}$ to $V_{CC} = 5.5\text{ V}$, but LV devices are guaranteed to function down to $V_{CC} = 1.0\text{ V}$ (with input levels GND or V_{CC}).

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.2\text{ V}$	0.9	-	-	0.9	-	V
		$V_{CC} = 2.0\text{ V}$	1.4	-	-	1.4	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	2.0	-	-	2.0	-	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.2\text{ V}$	-	-	0.3	-	0.3	V
		$V_{CC} = 2.0\text{ V}$	-	-	0.6	-	0.6	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	0.8	-	0.8	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = -100\ \mu\text{A}; V_{CC} = 1.2\text{ V}$	-	1.2	-	-	-	V
		$I_O = -100\ \mu\text{A}; V_{CC} = 2.0\text{ V}$	1.8	2.0	-	1.8	-	V
		$I_O = -100\ \mu\text{A}; V_{CC} = 2.7\text{ V}$	2.5	2.7	-	2.5	-	V
		$I_O = -100\ \mu\text{A}; V_{CC} = 3.0\text{ V}$	2.8	3.0	-	2.8	-	V
		$I_O = -100\ \mu\text{A}; V_{CC} = 4.5\text{ V}$	4.3	4.5	-	4.3	-	V
		$I_O = -6\text{ mA}; V_{CC} = 3.0\text{ V}$	2.4	2.82	-	2.2	-	V
$I_O = -12\text{ mA}; V_{CC} = 4.5\text{ V}$	3.6	4.2	-	3.5	-	V		

Table 6. Static characteristics ...continued
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 100 μA; V _{CC} = 1.2 V	-	0	-	-	-	V
		I _O = 100 μA; V _{CC} = 2.0 V	-	0	0.2	-	0.2	V
		I _O = 100 μA; V _{CC} = 2.7 V	-	0	0.2	-	0.2	V
		I _O = 100 μA; V _{CC} = 3.0 V	-	0	0.2	-	0.2	V
		I _O = 100 μA; V _{CC} = 4.5 V	-	0	0.2	-	0.2	V
		I _O = 6 mA; V _{CC} = 3.0 V	-	0.25	0.40	-	0.50	V
		I _O = 12 mA; V _{CC} = 4.5 V	-	0.35	0.55	-	0.65	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	-	1.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	20.0	-	40	μA
ΔI _{CC}	additional supply current	per input; V _I = V _{CC} - 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	500	-	850	μA
C _I	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics
 GND = 0 V; For test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	nA, nB to nY; see Figure 6 ^[2]						
		V _{CC} = 1.2 V	-	45	-	-	-	ns
		V _{CC} = 2.0 V	-	15	26	-	31	ns
		V _{CC} = 2.7 V	-	11	18	-	23	ns
		V _{CC} = 3.0 V to 3.6 V; C _L = 15 pF ^[3]	-	7	-	-	-	ns
		V _{CC} = 3.0 V to 3.6 V ^[3]	-	9.0	15	-	18	ns
		V _{CC} = 4.5 V to 5.5 V ^[3]	-	6.5	11	-	14	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC} ^[4]	-	22	-	-	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz, f_o = output frequency in MHz

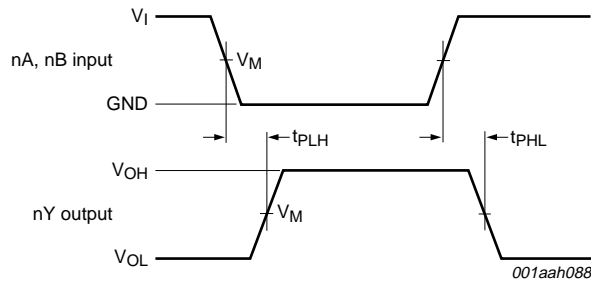
C_L = output load capacitance in pF

V_{CC} = supply voltage in V

N = number of inputs switching

Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

11. Waveforms



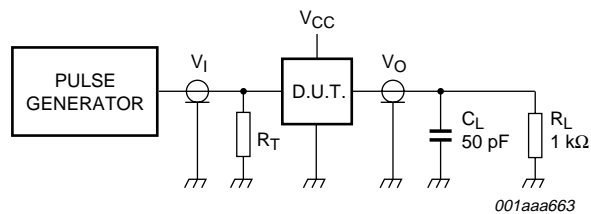
Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. The input (nA, nB) to output (nY) propagation delays

Table 8. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
< 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V to 3.6 V	1.5 V	1.5 V
≥ 4.5 V	$0.5V_{CC}$	$0.5V_{CC}$



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

Fig 7. Load circuit for switching times

Table 9. Test data

Supply voltage	Input	t_r, t_f
V_{CC}	V_I	t_r, t_f
< 2.7 V	V_{CC}	≤ 2.5 ns
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns
≥ 4.5 V	V_{CC}	≤ 2.5 ns

12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1

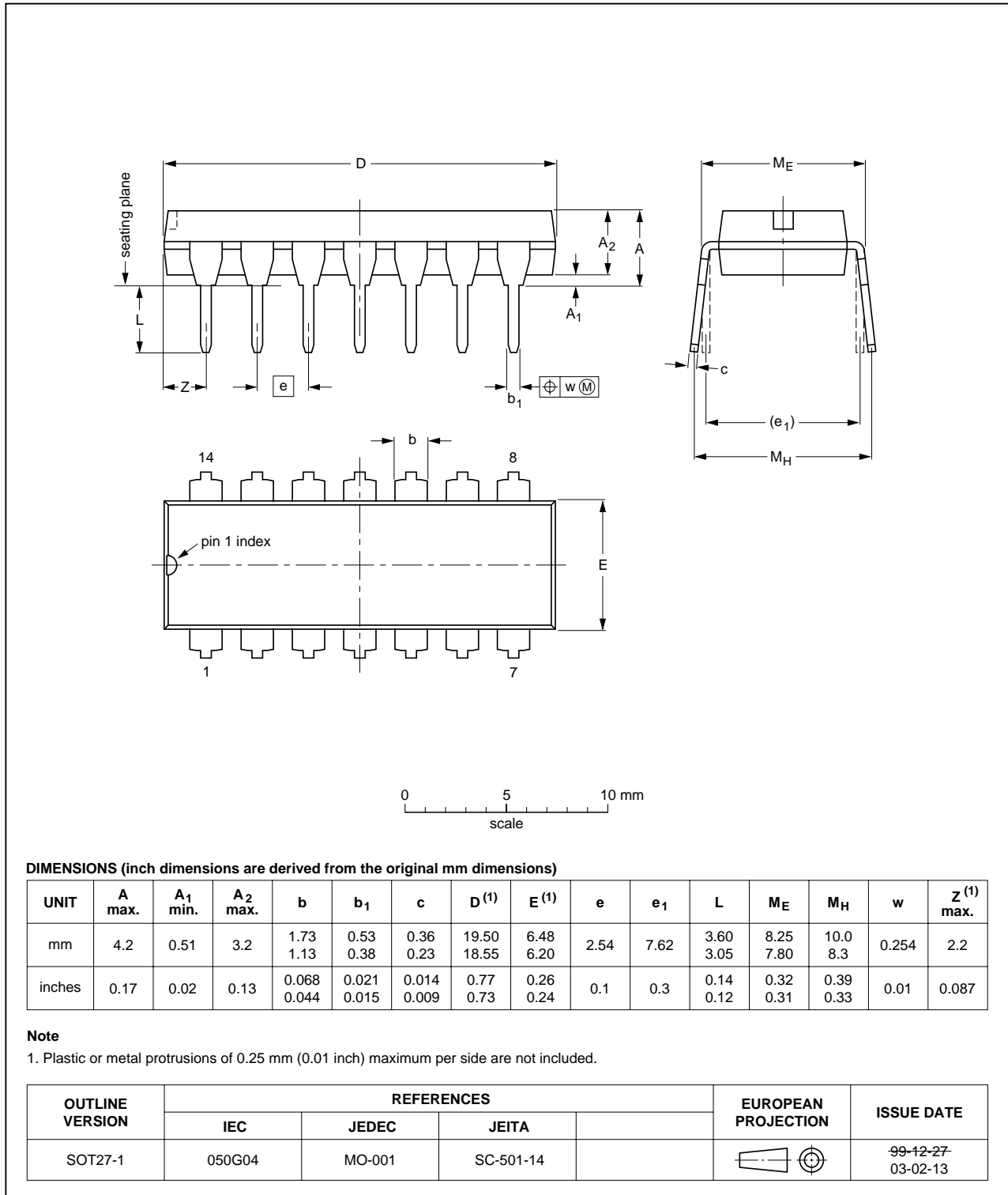


Fig 8. Package outline SOT27-1 (DIP14)

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

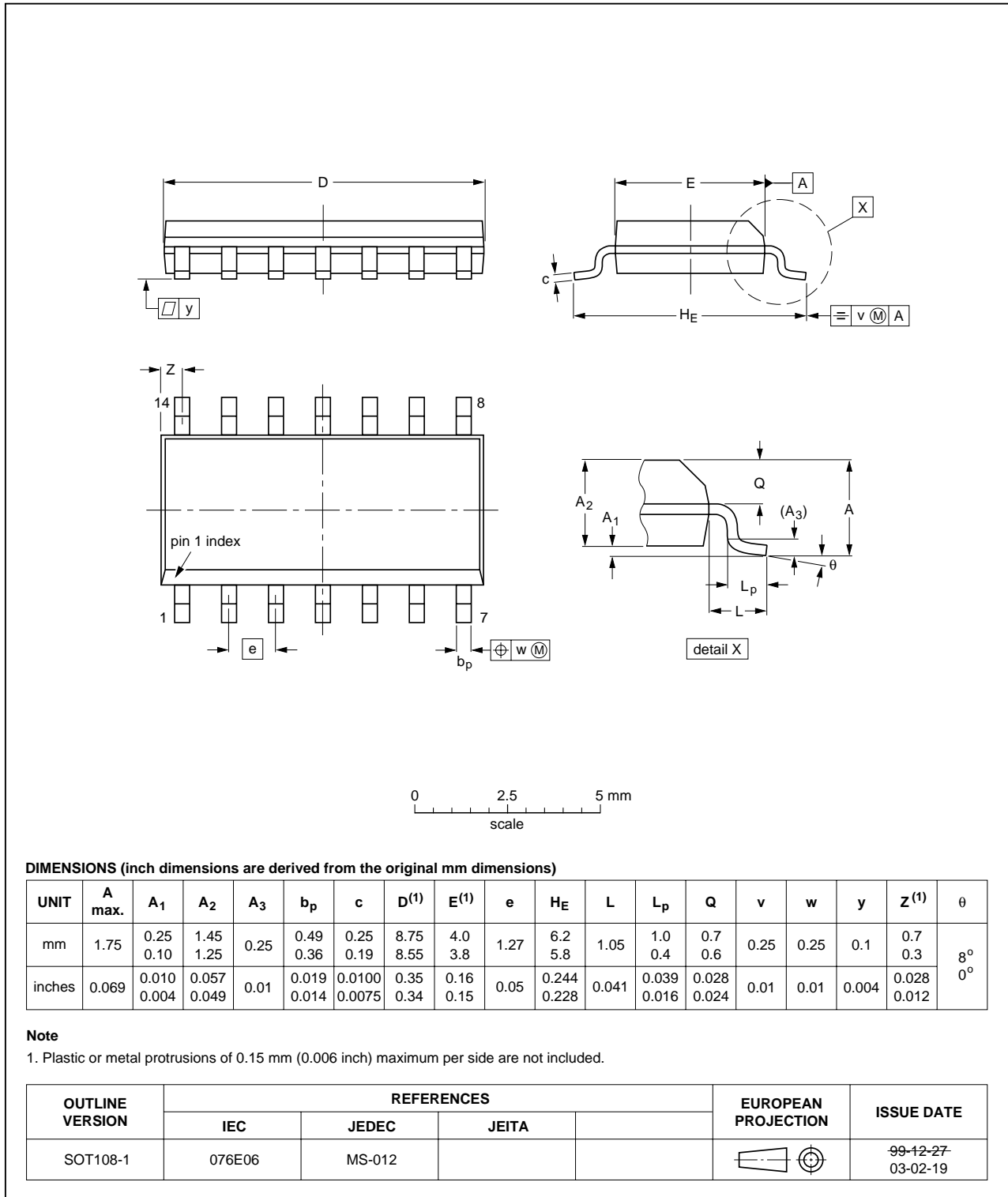


Fig 9. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1

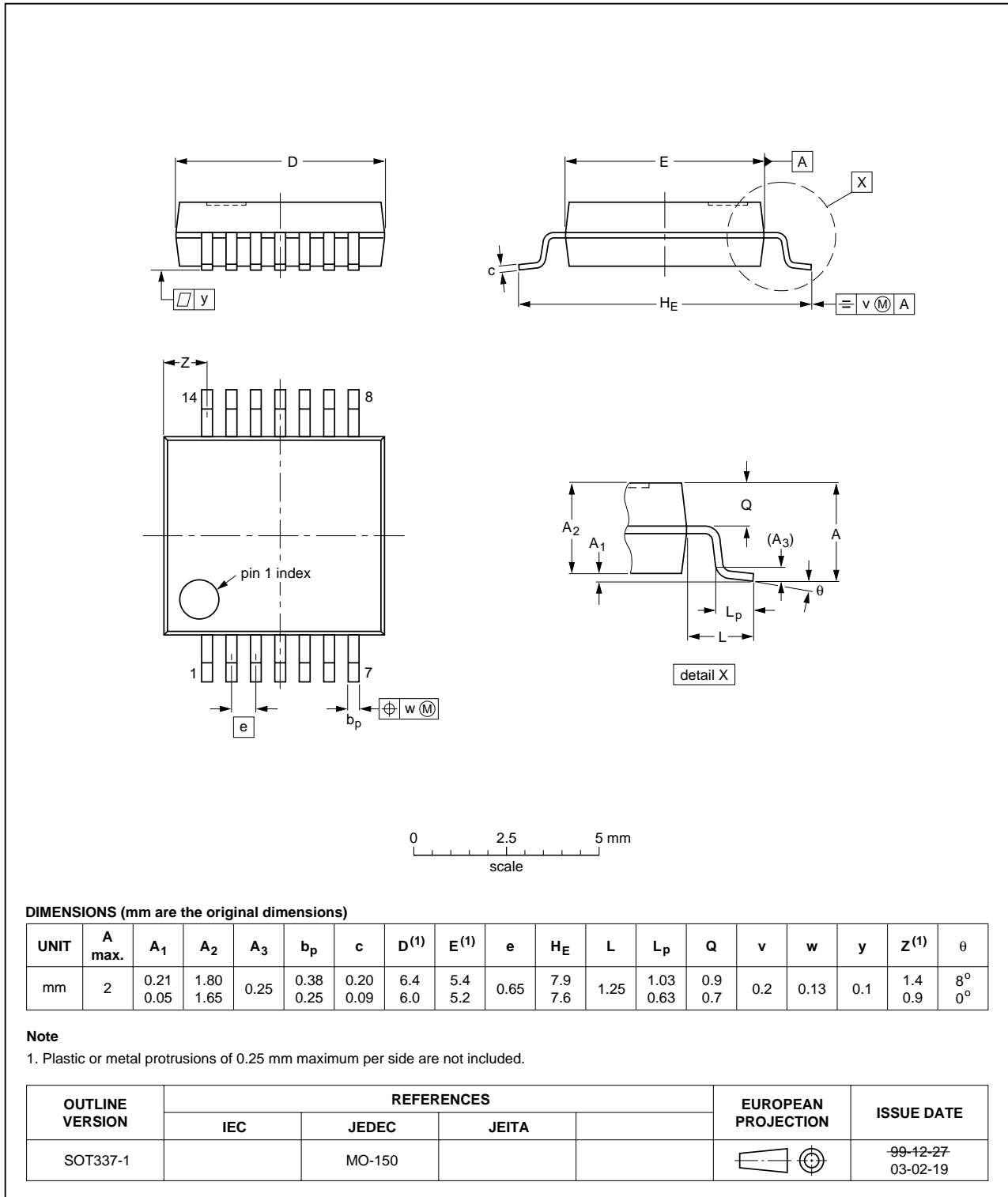


Fig 10. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

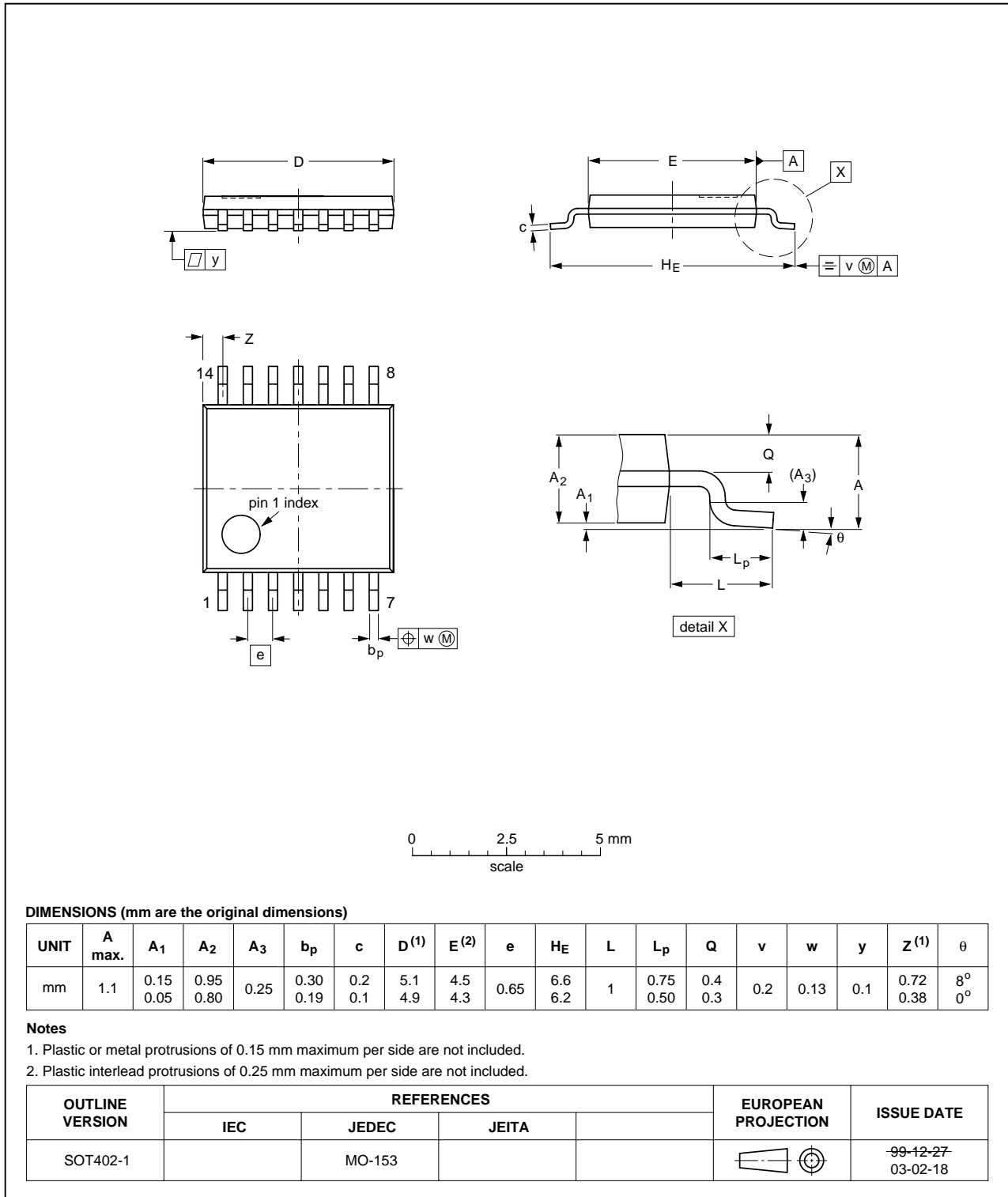


Fig 11. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

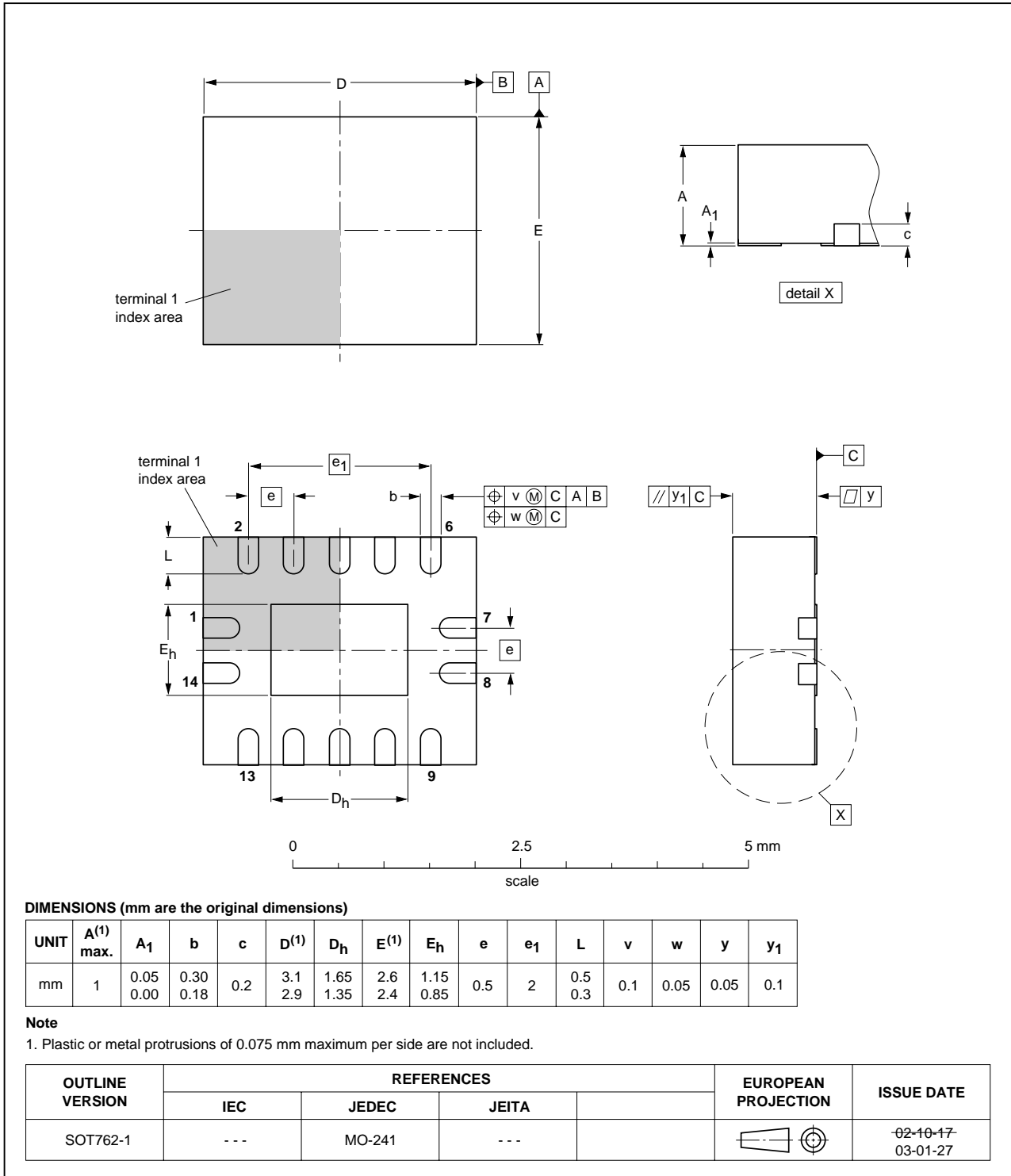


Fig 12. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV00_3	20071220	Product data sheet	-	74LV00_2
Modifications:	<ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• Section 3: DHVQFN14 package added.• Section 7: derating values added for DHVQFN14 package.• Section 12: outline drawing added for DHVQFN14 package.			
74LV00_2	19980420	Product specification	-	74LV00_1
74LV00_1	19970203	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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